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The invention relates to oxide semiconductor equipment and technology, in particular to *n*-butanol sensors based on $ZnO-Al_2O_3$ heterojunction.

The *n*-butanol sensor based on $ZnO-Al_2O_3$ heterojunction comprises a glass substrate (1), on the surface of which by the chemical synthesis method from a solution is deposited a ZnO film (2), and on its surface by vacuum thermal evaporation of Al [$Al(C_3H_7O)_3$] triisopropylate at the substrate temperature (1) equal to 450°C is deposited the Al_2O_3 film (3) with a thickness of 17-20 nm, on the surface of which meander-shaped contacts of Au-Cr (4) are deposited and processed by fast photon annealing at T=650°C, t=30 s.

Claims: 1
Fig.: 3